



100V 3.5A N-Channel MOSFET

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General Features

• $V_{DS} = 100V, I_D = 3.5A$ $R_{DS(ON)} < 130mΩ @ V_{GS} = 10V$ (96mΩ Typ)

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable
- Logic Level Shift

Package and Pin Configuration

 $R_{DS(ON)}$ <180m Ω @ V_{GS} =4.5V (140m Ω Typ)

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Circuit diagram



Marking:



- "₽" is TECHPUBLIC LOGO
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Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	I _D	3.5	Α	
Drain Current-Pulsed (Note 1)	I _{DM}	20	А	
Maximum Power Dissipation	P _D	1.5	W	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	

Thermal Characteristic

	N		
Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	100	°C/W



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Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	/ -		_ 1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	1 -	- /	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.0	1.5	2.0	V
Drain-Source On-State Resistance	Б	V_{GS} =10V, I_D =3A	-	96	130	mΩ
	R _{DS(ON)}	V _{GS} =4.5V, I _D =1A	/- \	140	180	
Forward Transconductance	g _{FS}	$V_{DS}=5V,I_{D}=3A$	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C _{oss}		-	24	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITIZ	-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V_{DD} =50V, R_L =19 Ω V_{GS} =10V, R_G =3 Ω	-	6	:=	nS
Turn-on Rise Time	t _r		-	4		nS
Turn-Off Delay Time	t _{d(off)}		-	20		nS
Turn-Off Fall Time	t _f		-	4		nS
Total Gate Charge	Qg	V _{DS} =50V,I _D =3A,	-	20		nC
Gate-Source Charge	Q _{gs}		-	2.1	1-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	$V_{GS}=0V,I_{S}=3A$	-	=0	1.2	V
Diode Forward Current (Note 2)	Is			3.5		Α





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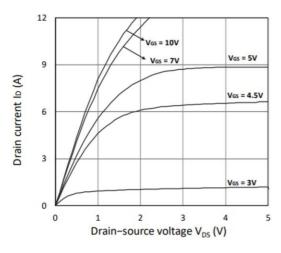


Figure 1. Output Characteristics

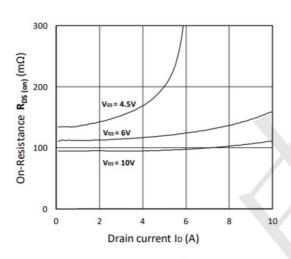


Figure 3. R_{DS} (ON) VS.I_D

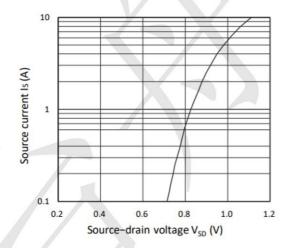


Figure 5. I_S VS.V_{SD}

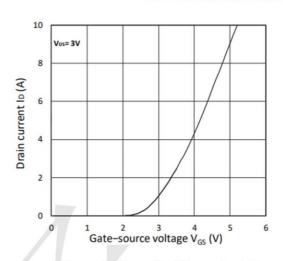


Figure 2. Transfer Characteristics

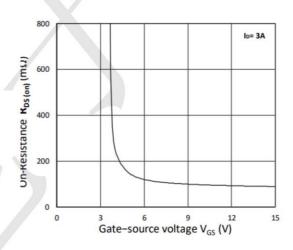


Figure 4. R_{DS} (ON) VS.V_{GS}

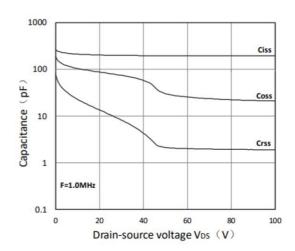
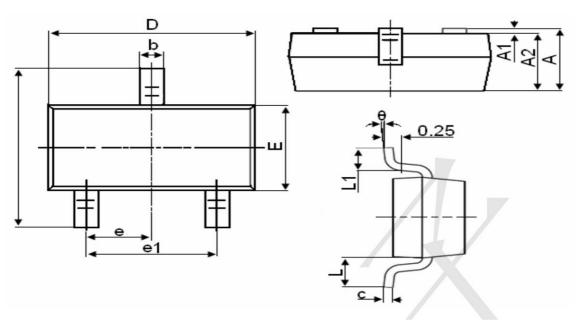


Figure 6. Capacitance Characteristics



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Package Outline Dimensions (SOT-23)



Sumb al	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
А	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.0	0.950TYP		
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

Marking:



"₽" is TECHPUBLIC LOGO

"3N" is Part number, fixed

"xx"is internal code

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